TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L52AE

VHF~UHF Band Low Noise Amplifier Applications

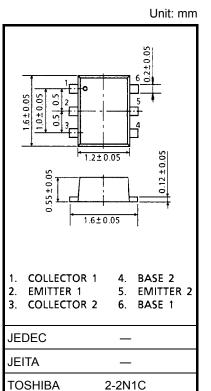
• Two devices are built in to the super-thin and extreme super mini (6 pins) package: ES6

Mounted Devices

	Q1: SSM (TESM)	Q2: SSM (TESM)
Three-pins (SSM/TESM) mold products are corresponded.	MT3S03AS	MT3S04AS
	(MT3S03AT)	(MT3S04AT)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Q1	Q2	Unit
Collector-base voltage	V_{CBO}	10	10	V
Collector-emitter voltage	V _{CEO}	5	5	V
Emitter-base voltage	V _{EBO}	2	2	V
Collector current	IC	40	40	mA
Base current	ΙΒ	10	10	mA
Collector power dissipation	P _C (Note 1)	100		mW
Junction temperature	Tj	125		°C
Storage temperature range	T _{stg}	-55~125		°C



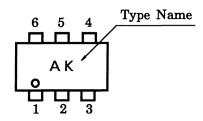
Weight: 0.003 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

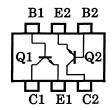
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total power dissipation of Q1 and Q2.

Marking



Pin Assignment (top view)



Electrical Characteristics Q1 (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ	
Emitter cut-off current	I _{EBO}	V _{EB} = 1 V, I _C = 0	_	_	1	μА	
DC current gain	h _{FE}	V _{CE} = 1 V, I _C = 5 mA	80	_	160		
Transition frequency	f _T (1)	V _{CE} = 1 V, I _C = 5 mA	5	7	_	GHz	
	f _T (2)	$V_{CE} = 3 \text{ V, } I_{C} = 10 \text{ mA}$	7	10	_		
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	5	_	dB	
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 2 \text{ GHz}$	3	6.5	_		
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	- dB	
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}, f = 2 \text{ GHz}$	_	1.4	2.2		
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.8	1.15	pF	

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Electrical Characteristics Q2 (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 1 V, I _C = 0	_	_	1	μА
DC current gain	h _{FE}	V _{CE} = 1 V, I _C = 5 mA	80	_	160	
Transition frequency	f _T (1)	V _{CE} = 1 V, I _C = 5 mA	2	4.5	_	GHz
	f _T (2)	V _{CE} = 3 V, I _C = 7 mA	5	7	_	
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	8.5	_	dB
	S _{21e} ² (2)	V _{CE} = 3 V, I _C = 20 mA, f = 1 GHz	7.5	11	_	uв
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	1.3	2.2	- dB
	NF (2)	V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	_	1.2	2	
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note 2)	_	0.9	1.25	pF

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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20070701-EN GENERAL

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